Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Very fast switching
- Enhanced power dissipation capability: Ptot = 890 mW
- ElectroStatic Discharge (ESD) protection 2 kV HBM

3. Applications

- Relay driver
- High speed line driver
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	-3.3	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -2.8 A; T_j = 25 °C		-	67	78	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².





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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u> </u>	D I
2	S	source		
3	D	drain	1	G S 017aaa259

6. Ordering information

Table 3. Ordering information

Type number	Package	age					
	Name	Description	Version				
PMV65XPE	TO-236AB	plastic surface-mounted package; 3 leads	SOT23				

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV65XPE	%KE

[1] % = placeholder for manufacturing site code

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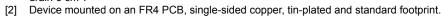
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-3.3	Α
		V_{GS} = -4.5 V; T_{amb} = 25 °C	[1]	-	-2.8	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-1.8	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	-12	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	480	mW
			[1]	-	890	mW
		T _{sp} = 25 °C		-	6250	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain o	liode		1	-	1	
Is	source current	T _{amb} = 25 °C	[1]	-	-0.9	Α

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



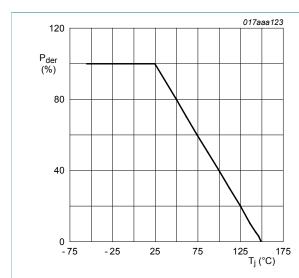


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

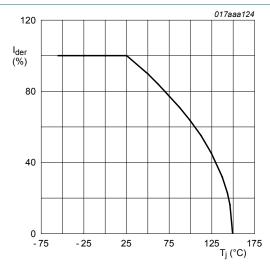


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100~\%$$

PMV65XPE

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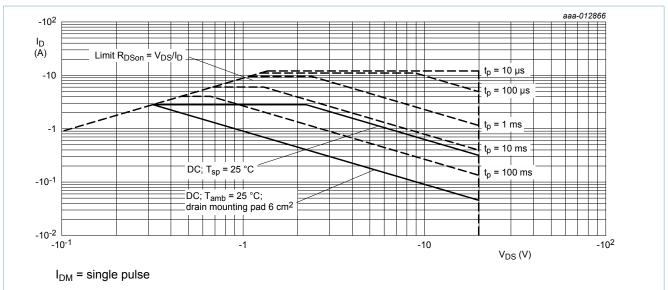


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	<u> </u>	[1]	-	230	260	K/W
	from junction to ambient		[2]	-	120	140	K/W
	anibient	in free air; t ≤ 5 s	[2]	-	85	100	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	15	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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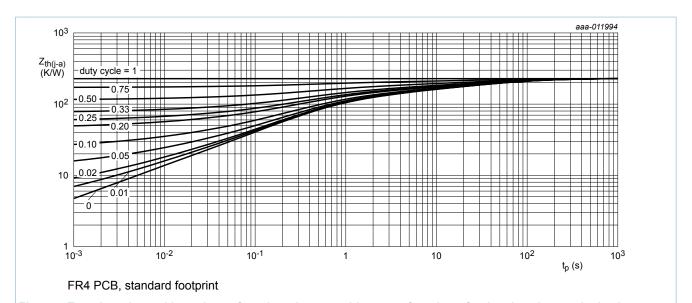


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

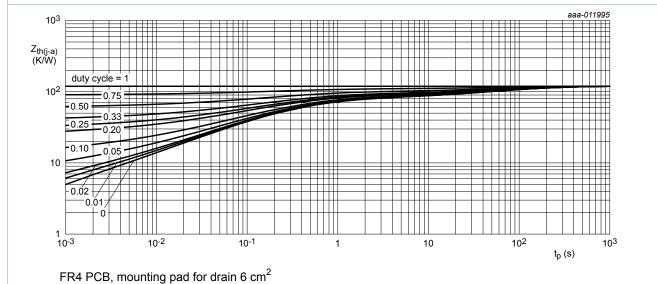


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		,			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	-0.75	-1	-1.25	V
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μA
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μΑ
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μΑ
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_D = -2.8 A; T_j = 25 °C	-	67	78	mΩ
	resistance	V _{GS} = -4.5 V; I _D = -2.8 A; T _j = 150 °C	-	98	114	mΩ
		V_{GS} = -2.5 V; I_D = -2.2 A; T_j = 25 °C	-	99	125	mΩ
9fs	forward transconductance	V_{DS} = -10 V; I_D = -2 A; T_j = 25 °C	-	7.4	-	S
R_G	gate resistance	f = 1 MHz	-	11.6	-	Ω
Dynamic c	haracteristics		1	'		
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -2.8 A; V_{GS} = -4.5 V;	-	5	9	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	1.1	-	nC
Q_{GD}	gate-drain charge		-	1.1	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	618	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	80	-	pF
C _{rss}	reverse transfer capacitance		-	58	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -2.8 A; V_{GS} = -4.5 V;	-	7	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	19	-	ns
t _{d(off)}	turn-off delay time		-	36	-	ns
t _f	fall time		-	17	-	ns
Source-dra	ain diode		1	-	1	-
V _{SD}	source-drain voltage	$I_S = -0.85 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.75	-1.2	V

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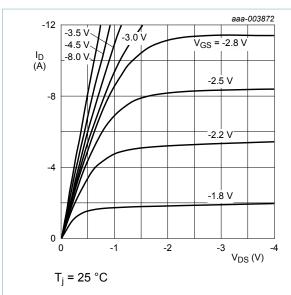
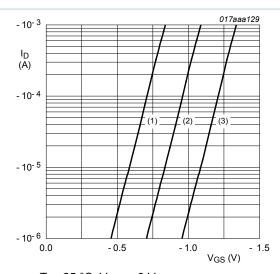


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



$$T_j$$
 = 25 °C; V_{DS} = -3 V

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

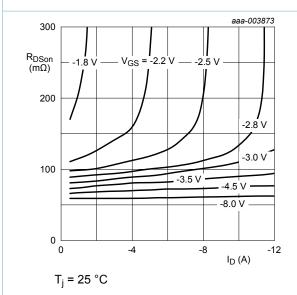


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

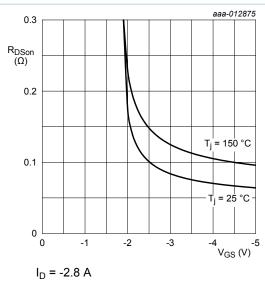


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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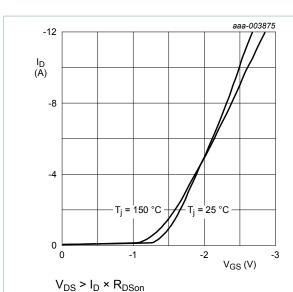


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

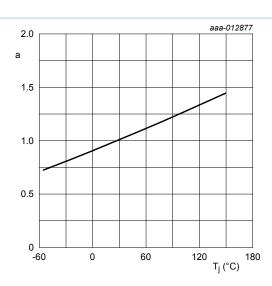


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

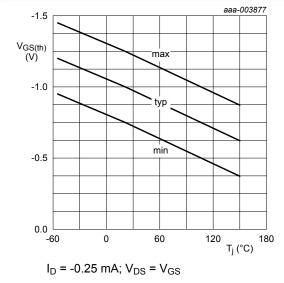
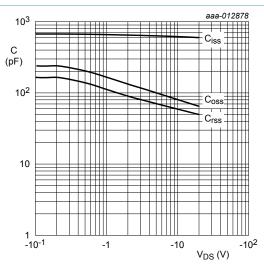


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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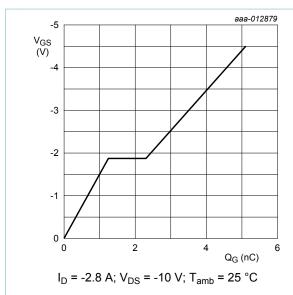


Fig. 14. Gate-source voltage as a function of gate charge; typical values

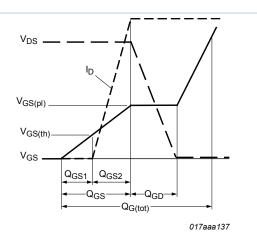


Fig. 15. MOSFET transistor: Gate charge waveform definitions

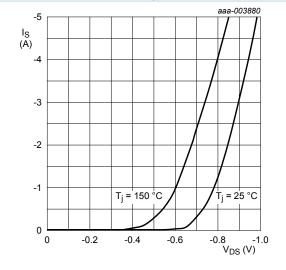
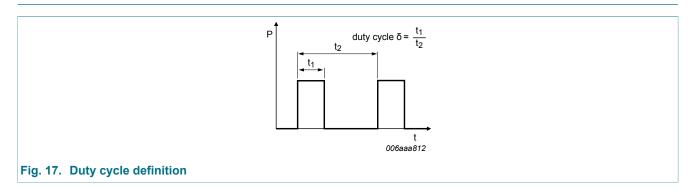


Fig. 16. Source current as a function of source-drain voltage; typical values

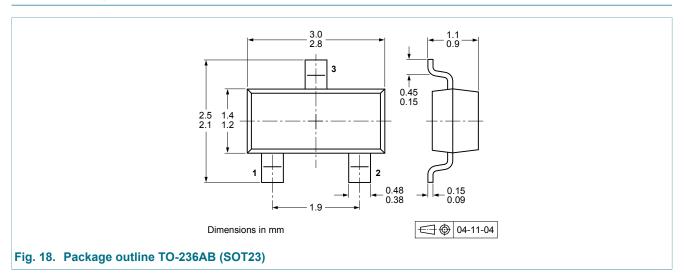
 $V_{GS} = 0 V$

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11. Test information

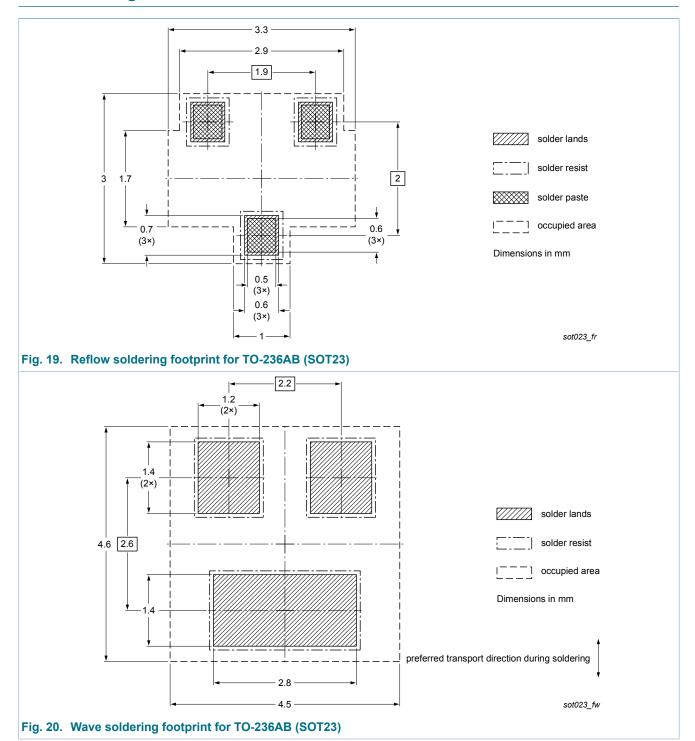


12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV65XPE v.1	20140425	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

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